

Amendment to the Claims

1. (Currently Amended) A method of mounting a semiconductor laser component having a light emitting portion on a submount through a bonding member, the method ~~comprising steps of comprising:~~

setting the submount having a bonding member at a mount surface thereof on a heating table;

heating the submount to bring the bonding member up to a temperature that is more than a melting point thereof;

positioning the semiconductor laser component on the mount surface of the submount, wherein the semiconductor laser component is positioned by means of a ~~by a collet means,~~ collet;

pressure-bonding the semiconductor laser component on the mount surface of the submount by the ~~collet means~~; and

~~heating again reheating~~ the submount on the heating table without pressure by the collet after the bonding member is completely coagulated.

2. (Currently Amended) A method of mounting a semiconductor laser component on a submount through a bonding member according to claim 1, wherein, during the reheating operation, the bonding member is heated up to ~~a melting~~ the melting point of the bonding member.

3. (Currently Amended) A method of mounting a semiconductor laser component on a submount through a bonding member according to claim 1, wherein a plurality of semiconductor laser ~~elements components are bonded to a plurality of submounts, respectively, and the submounts are reheated together~~ bonded to the submounts are heated again together.

4. (Currently Amended) A method of mounting a semiconductor laser component on a submount through a bonding member according to claim 1, wherein a method of the first heating operation is different from that of the second reheating operation-heating.
5. (Currently Amended) A method of mounting a semiconductor laser component on a submount through a bonding member according to claim 1, wherein the second heating-reheating operation is carried out by at least one selected from the group consisting of hot-air heating, ohmic-resistance heating, and high-frequency heating.
6. (Original) A method of mounting a semiconductor laser component on a submount through a bonding member according to claim 1, wherein the bonding member is a Pb-free solder member.
7. (Original) A method of mounting a semiconductor laser component on a submount through a bonding member according to claim 1, wherein the semiconductor laser component is a GaN, GaAs or AlInGaP system semiconductor element, and the submount is made of Si or SiC.
- 8.(Withdrawn) A semiconductor laser device having a semiconductor laser component mounted on a circuit board through a submount, wherein the semiconductor laser component is mounted on the bonding surface of the submount through a bonding member by pressure bonding without a residual stress due to the pressure bonding the semiconductor laser device on the submount.
- 9.(Withdrawn) A semiconductor laser device having a semiconductor laser component mounted on a circuit board through a submount according to claim 8, wherein the

submount is provided with an Au coating at the bonding surface thereof.

10.(Withdrawn) A semiconductor laser device having a semiconductor laser component mounted on a circuit board through a submount according to claim 8, wherein the laser component is pressure bonded on the submount by a Pb-free bonding member.

11.(Withdrawn) A semiconductor laser device having a semiconductor laser component mounted on a circuit board through a submount according to claim 8, wherein the bonding member is a solder member selected from the group consisting of Au-Sn, Sn-Ag-Bi-In, Sn-Zn-Bi and Sn-Bi-Ag.

12.(Withdrawn) A semiconductor laser device having a semiconductor laser component on a circuit board through a submont according to claim 10,wherein the solder member is pressure bonded up to about 1 to 1.5 μm .